

# Paul Crozat

## List of Publications by Year in descending order

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175  
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4,744  
citations

117625

34  
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102487

66  
g-index

176  
all docs

176  
docs citations

176  
times ranked

4004  
citing authors

#	ARTICLE	IF	CITATIONS
1	42 GHz pin Germanium photodetector integrated in a silicon-on-insulator waveguide. Optics Express, 2009, 17, 6252.	3.4	456
2	Zero-bias 40Gbit/s germanium waveguide photodetector on silicon. Optics Express, 2012, 20, 1096.	3.4	368
3	Single-Shot Time-Resolved Measurements of Nanosecond-Scale Spin-Transfer Induced Switching: Stochastic Versus Deterministic Aspects. Physical Review Letters, 2008, 100, 057206.	7.8	219
4	Current-Driven Vortex Oscillations in Metallic Nanocontacts. Physical Review Letters, 2008, 100, 257201.	7.8	209
5	High speed and high responsivity germanium photodetector integrated in a Silicon-On-Insulator microwaveguide. Optics Express, 2007, 15, 9843.	3.4	196
6	Integrated germanium optical interconnects on silicon substrates. Nature Photonics, 2014, 8, 482-488.	31.4	196
7	Phase Coherent Precessional Magnetization Reversal in Microscopic Spin Valve Elements. Physical Review Letters, 2003, 90, 017201.	7.8	155
8	Current-driven microwave oscillations in current perpendicular-to-plane spin-valve nanopillars. Applied Physics Letters, 2006, 88, 192507.	3.3	114
9	Vector network analyzer ferromagnetic resonance of thin films on coplanar waveguides: Comparison of different evaluation methods. Journal of Applied Physics, 2007, 101, 074505.	2.5	112
10	Germanium avalanche receiver for low power interconnects. Nature Communications, 2014, 5, 4957.	12.8	112
11	40 Gbit/s low-loss silicon optical modulator based on a pipin diode. Optics Express, 2012, 20, 10591.	3.4	99
12	Terahertz radiation from heavy-ion-irradiated In <sub>0.53</sub> Ga <sub>0.47</sub> As photoconductive antenna excited at 1.55 μm. Applied Physics Letters, 2005, 87, 193510.	3.3	90
13	GaN/AlGaIn intersubband optoelectronic devices. New Journal of Physics, 2009, 11, 125023.	2.9	84
14	Integrated waveguide PIN photodiodes exploiting lateral Si/Ge/Si heterojunction. Optics Express, 2017, 25, 19487.	3.4	84
15	Recent Progress in High-Speed Silicon-Based Optical Modulators. Proceedings of the IEEE, 2009, 97, 1199-1215.	21.3	83
16	Ultrahigh speed germanium-on-silicon-on-insulator photodetectors for 1.31 and 1.55 μm operation. Applied Physics Letters, 2005, 87, 231109.	3.3	81
17	High-temperature superconducting surface coil for in vivo microimaging of the human skin. Magnetic Resonance in Medicine, 2001, 45, 376-382.	3.0	68
18	Low loss 40 Gbit/s silicon modulator based on interleaved junctions and fabricated on 300 mm SOI wafers. Optics Express, 2013, 21, 22471.	3.4	64

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19	Subnanosecond magnetization reversal in magnetic nanopillars by spin angular momentum transfer. Applied Physics Letters, 2004, 85, 5358-5360.	3.3	61
20	Agility of vortex-based nanocontact spin torque oscillators. Applied Physics Letters, 2009, 95, .	3.3	60
21	Continuous wave terahertz generation up to 2THz by photomixing on ion-irradiated In <sub>0.53</sub> Ga <sub>0.47</sub> As at 1.55 $\mu$ m wavelengths. Applied Physics Letters, 2007, 91, .	3.3	58
22	GaN/AlGaIn waveguide quantum cascade photodetectors at 1.55 $\mu$ m with enhanced responsivity and 40GHz frequency bandwidth. Applied Physics Letters, 2013, 102, .	3.3	55
23	Short-wavelength intersubband electroabsorption modulation based on electron tunneling between GaN/AlN coupled quantum wells. Applied Physics Letters, 2007, 90, 223511.	3.3	54
24	High-performance waveguide-integrated germanium PIN photodiodes for optical communication applications [Invited]. Photonics Research, 2013, 1, 140.	7.0	54
25	25Gbps low-voltage hetero-structured silicon-germanium waveguide pin photodetectors for monolithic on-chip nanophotonic architectures. Photonics Research, 2019, 7, 437.	7.0	54
26	Ten Gbit/s ring resonator silicon modulator based on interdigitated PN junctions. Optics Express, 2011, 19, 14690.	3.4	53
27	High-speed operation of GaN/AlGaIn quantum cascade detectors at 1.55 $\mu$ m. Applied Physics Letters, 2008, 93, .	3.3	52
28	Time-resolved zero field vortex oscillations in point contacts. Applied Physics Letters, 2009, 95, .	3.3	50
29	Experimental demonstration of complete photonic band gap in graphite structure. Applied Physics Letters, 1997, 71, 1780-1782.	3.3	45
30	Magnetization switching by spin torque using subnanosecond current pulses assisted by hard axis magnetic fields. Applied Physics Letters, 2006, 88, 152502.	3.3	43
31	A 40 Gbit/s optical link on a 300-nm silicon platform. Optics Express, 2014, 22, 6674.	3.4	39
32	Coherent suppression of magnetic ringing in microscopic spin valve elements. Applied Physics Letters, 2002, 80, 3781-3783.	3.3	36
33	High performance 100 nm T-gate strained Si/Si <sub>0.6</sub> Ge <sub>0.4</sub> n-MODFET. Solid-State Electronics, 2003, 47, 283-289.	1.4	36
34	Frequency shift keying in vortex-based spin torque oscillators. Journal of Applied Physics, 2011, 109, 083940.	2.5	36
35	Temperature study of the spin-transfer switching speed from dc to 100ps. Journal of Applied Physics, 2005, 98, 053904.	2.5	34
36	Instability threshold versus switching threshold in spin-transfer-induced magnetization switching. Physical Review B, 2005, 71, .	3.2	34

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37	40 Gbps heterostructure germanium avalanche photo receiver on a silicon chip. <i>Optica</i> , 2020, 7, 775.	9.3	34
38	Low voltage 25Gbps silicon Mach-Zehnder modulator in the O-band. <i>Optics Express</i> , 2017, 25, 11217.	3.4	33
39	Precharging strategy to accelerate spin-transfer switching below the nanosecond. <i>Applied Physics Letters</i> , 2005, 86, 062505.	3.3	32
40	Electrooptical Modulator at Telecommunication Wavelengths Based on GaN/AlN Coupled Quantum Wells. <i>IEEE Photonics Technology Letters</i> , 2008, 20, 724-726.	2.5	31
41	Two- and three-dimensional microcoil fabrication process for three-axis magnetic sensors on flexible substrates. <i>Sensors and Actuators A: Physical</i> , 2006, 132, 2-7.	4.1	30
42	Temperature Dependences of the Resistivity and the Ferromagnetic Resonance Linewidth in Permalloy Thin Films. <i>IEEE Transactions on Magnetics</i> , 2006, 42, 3323-3325.	2.1	30
43	Emission characteristics of ion-irradiated In <sub>0.53</sub> Ga <sub>0.47</sub> As based photoconductive antennas excited at 1.55 $\mu\text{m}$ . <i>Optics Express</i> , 2007, 15, 8943.	3.4	30
44	Ion-irradiated In <sub>0.53</sub> Ga <sub>0.47</sub> As photoconductive antennas for THz generation and detection at 1.55 $\mu\text{m}$ wavelength. <i>Comptes Rendus Physique</i> , 2008, 9, 142-152.	0.9	30
45	Thermal stability of ion-irradiated InGaAs with (sub-) picosecond carrier lifetime. <i>Applied Physics Letters</i> , 2003, 82, 856-858.	3.3	28
46	Ultrafast response ( $\sim 2.2$ ps) of ion-irradiated InGaAs photoconductive switch at 1.55 $\mu\text{m}$ . <i>Applied Physics Letters</i> , 2003, 83, 5551-5553.	3.3	26
47	Auto-oscillation and narrow spectral lines in spin-torque oscillators based on MgO magnetic tunnel junctions. <i>Journal of Applied Physics</i> , 2009, 106, 103921.	2.5	25
48	Comprehensive Study on Chip-Integrated Germanium Pin Photodetectors for Energy-Efficient Silicon Interconnects. <i>IEEE Journal of Quantum Electronics</i> , 2020, 56, 1-9.	1.9	25
49	Spin transfer oscillators emitting microwave in zero applied magnetic field. <i>Journal of Applied Physics</i> , 2007, 101, 063916.	2.5	24
50	Open-Circuit One-Port Network Analyzer Ferromagnetic Resonance. <i>IEEE Transactions on Magnetics</i> , 2008, 44, 3265-3268.	2.1	24
51	40 Gb/s surface-illuminated Ge-on-Si photodetectors. <i>Applied Physics Letters</i> , 2009, 95, .	3.3	22
52	Electroluminescence spectroscopy of AlGaAs/InGaAs and AlGaAs/GaAs high electron mobility transistors. <i>Journal of Applied Physics</i> , 1995, 77, 2184-2189.	2.5	21
53	Four noise parameter determination method for transistors based on the frequency dependence of the noise figure. <i>Electronics Letters</i> , 1998, 34, 1612.	1.0	21
54	0.3 dB minimum noise figure at 2.5 GHz of 0.13 $\mu\text{m}$ Si/Si <sub>0.58</sub> Ge <sub>0.42</sub> n-MODFETs. <i>Electronics Letters</i> , 2001, 37, 1089.	1.0	21

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55	Inductive measurement of the high frequency permeability of a Permalloy thin film. Journal of Magnetism and Magnetic Materials, 2004, 272-276, 290-292.	2.3	20
56	Metal-semiconductor-metal Ge photodetectors integrated in silicon waveguides. Applied Physics Letters, 2008, 92, 151114.	3.3	20
57	Ultrafast terahertz detectors based on three-dimensional meta-atoms. Optica, 2017, 4, 1451.	9.3	20
58	DC and high frequency performance of 0.1[μm] n-type Si <sup>0.6</sup> Ge <sup>0.4</sup> MODFET with f <sub>MAX</sub> =188 GHz at 300K and f <sub>MAX</sub> =230 GHz at 50K. Electronics Letters, 2003, 39, 149.	1.0	19
59	0.1 [μm] gate length p-type Ge/Si <sub>0.4</sub> Ge <sub>0.6</sub> MODFET with 135 GHz f <sub>max</sub> . Electronics Letters, 2000, 36, 1428.	1.0	18
60	Microwave properties of silicon junction tunnel diodes grown by molecular beam epitaxy. IEEE Electron Device Letters, 2002, 23, 357-359.	3.9	18
61	Optical phase detection in a 4-N,N-dimethylamino-4'-nitro-methyl-stilbazolium tosylate crystal for terahertz time domain spectroscopy system at 1.55 μm wavelength. Applied Physics Letters, 2010, 97, .	3.3	18
62	Spin-torque switching window, thermal stability, and material parameters of MgO tunnel junctions. Applied Physics Letters, 2011, 98, 162502.	3.3	18
63	Noise parameters of InP-based double heterojunction base-collector self-aligned bipolar transistors. , 1999, 9, 195-197.		17
64	Magnetic anisotropy of epitaxial MgO/Fe/MgO films studied by network analyzer ferromagnetic resonance. Journal of Applied Physics, 2005, 98, 023901.	2.5	17
65	Photomixing at 1.55 μm in ion-irradiated In(0.53)Ga(0.47)As on InP. Optics Express, 2006, 14, 1856.	3.4	17
66	Auto-oscillation threshold and line narrowing in MgO-based spin-torque oscillators. Europhysics Letters, 2009, 87, 57001.	2.0	17
67	Ultra-fast magnetization reversal in magnetic nano-pillars by spin-polarized current. Journal of Magnetism and Magnetic Materials, 2005, 286, 77-82.	2.3	16
68	THz surface plasmon modes on planar Goubau lines. Optics Express, 2012, 20, 8466.	3.4	16
69	Lateral and Longitudinal Finite Size Effects in NA-FMR Measurements. IEEE Transactions on Magnetics, 2006, 42, 3321-3322.	2.1	14
70	Photonic band gap materials for devices in the microwave domain. IEEE Transactions on Magnetics, 1998, 34, 3028-3031.	2.1	13
71	Conduction mechanisms in ion-irradiated InGaAs layers. Journal of Applied Physics, 2005, 97, 063515.	2.5	13
72	Picosecond large signal switching characteristics of a pseudomorphic AlGaAs/InGaAs modulated doped field effect transistor. Applied Physics Letters, 1992, 61, 1187-1189.	3.3	12

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73	Comparison of radio-frequency and microwave superconducting properties of YBaCuO dedicated to magnetic resonance imaging. IEEE Transactions on Applied Superconductivity, 1999, 9, 4695-4701.	1.7	12
74	Precessional magnetization reversal in microscopic spin valve cells. IEEE Transactions on Magnetics, 2002, 38, 2480-2483.	2.1	12
75	SiGe heterojunction bipolar transistor issues towards high cryogenic performances. Cryogenics, 2009, 49, 620-625.	1.7	12
76	Low temperature electroluminescence spectroscopy of high electron mobility transistors on InP. Journal of Applied Physics, 1996, 80, 464-469.	2.5	11
77	Fabrication and characterization of 1.55 $\mu\text{m}$ single transverse mode large diameter electrically pumped VECSEL. Optical and Quantum Electronics, 2007, 38, 1269-1278.	3.3	11
78	Large-signal model of picosecond FETs and measurement of the step response. IEEE Transactions on Microwave Theory and Techniques, 1989, 37, 1460-1465.	4.6	10
79	50 [ohm sign] noise measurements with full receiver calibration without tuner. Electronics Letters, 1996, 32, 261.	1.0	10
80	Gigahertz modulation of tunable terahertz radiation from photomixers driven at telecom wavelengths. Applied Physics Letters, 2008, 93, .	3.3	10
81	Two-port vectorial terahertz electro-optic sampling system. Applied Physics Letters, 2008, 92, .	3.3	9
82	Electrical time-domain observation of magnetization switching induced by spin transfer in magnetic nanostructures (invited). Journal of Applied Physics, 2008, 103, 07A723.	2.5	9
83	Time response of small capacitance tunnel junctions and the simulation of fast logic circuits. IEEE Transactions on Magnetics, 1983, 19, 1221-1224.	2.1	8
84	Precise determination of open circuit capacitance of coplanar probes for on-wafer automatic network analyser measurements. Electronics Letters, 1991, 27, 1476.	1.0	8
85	A picosecond Josephson junction model for circuit simulation. Revue De Physique Appliqu�e, 1986, 21, 319-326.	0.4	8
86	Coherently suppressed ringing of the magnetization in microscopic giant magnetoresistive devices. Journal of Applied Physics, 2002, 91, 8043.	2.5	7
87	Radiofrequency Characterization of Gold/Ferroelectric SrBi <sub>2</sub> Nb <sub>2</sub> O <sub>9</sub> Heterostructures for Tunable Devices. Ferroelectrics, 2003, 288, 103-110.	0.6	7
88	Precessional direct-write switching in micrometer-sized magnetic tunnel junctions. Journal of Applied Physics, 2005, 97, 074503.	2.5	7
89	Single-mode in-gap emission of medium-width photonic crystal waveguides on InP substrate. Optics Express, 2005, 13, 6947.	3.4	7
90	Characteristics of GaAs/AlGaAs HEMT's fabricated by X-ray lithography. IEEE Transactions on Electron Devices, 1996, 43, 175-178.	3.0	6

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91	Feasibility of picosecond electrical sampling using GaAs FET. IEEE Transactions on Instrumentation and Measurement, 2000, 49, 172-177.	4.7	6
92	42 GHz waveguide germanium-on-silicon vertical PIN photodetector. , 2008, , .		6
93	European HELIOS project: Silicon photonic photodetector integration. , 2009, , .		6
94	Low timing jitter of gain- and Q-switched laser diodes for high bit rate OTDM applications. Electronics Letters, 1997, 33, 1875.	1.0	5
95	A low-noise cryogenically-cooled 8â€“12 GHz HEMT Amplifier for future space applications. Journal of Infrared, Millimeter and Terahertz Waves, 1997, 18, 85-99.	0.6	5
96	Electrical properties of 1.55â€“m sensitive ion-irradiated InGaAs with subpicosecond carrier lifetime. Electronics Letters, 2003, 39, 681.	1.0	5
97	Impedance up to 6 GHz in La <sub>0.67</sub> Sr <sub>0.33</sub> MnO <sub>3</sub> thin films. Applied Physics Letters, 2003, 83, 2596-2598.	3.3	5
98	Experimental study of current-driven vortex oscillations in magnetic nanocontacts. Proceedings of SPIE, 2009, , .	0.8	5
99	40Gbit/s germanium waveguide photodetector on silicon. , 2012, , .		5
100	Cryogenic investigation of gate leakage and RF performances down to 50 K of 0.2 Î¼m AlInAs/GaInAs/InP HEMTs. Electronics Letters, 1993, 29, 2152.	1.0	5
101	Enhancements and Degradations in Ultrashort Gate GaAs and InP HEMTs Properties at Cryogenic Temperatures : an Overview. European Physical Journal Special Topics, 1996, 06, C3-145-C3-149.	0.2	5
102	Scaling behavior of delta-doped AlGaAs/InGaAs high electron mobility transistors with gatelengths down to 60 nm and source-drain gaps down to 230 nm. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1993, 11, 1203.	1.6	4
103	Electric parameter evolutions against gatelength and bias in ultrashort gate AlGaAs/GaAs HEMTs. Electronics Letters, 1993, 29, 642.	1.0	4
104	De-embedded ultra-low noise 0.1 [micro sign]m gate length Ge/Si <sub>0.4</sub> Ge <sub>0.6</sub> p-MODFET. Electronics Letters, 2001, 37, 1478.	1.0	4
105	MESFET large-signal model based on small-signal measurements for time-domain CAD. Electronics Letters, 1988, 24, 973.	1.0	4
106	Condition of modal analysis in time domain of lossy coupled lines. Electronics Letters, 1988, 24, 1289.	1.0	4
107	Measuring a population of spin waves from the electrical noise of an inductively coupled antenna. Physical Review B, 2022, 105, .	3.2	4
108	Cryogenic behavior of Ultrashort gate AlGaAs/GaAs and pseudomorphic AlGaAs/InGaAs/GaAs HEMT's. Microelectronic Engineering, 1992, 19, 861-864.	2.4	3

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109	Microwave performances of silicon heterostructure-FETs. Applied Surface Science, 2004, 224, 370-376.	6.1	3
110	35 GHz bandwidth germanium-on-silicon photodetector. , 0, , .		3
111	40Gbit/s Germanium Waveguide Photodiode. , 2013, , .		3
112	Silicon photonic spiral shape resonator applied to the optoelectronic oscillator. IET Optoelectronics, 2019, 13, 303-307.	3.3	3
113	High-temperature superconducting receiver coil for NMR skin imaging. European Physical Journal Special Topics, 1998, 08, Pr3-245-Pr3-248.	0.2	3
114	Ultrahigh Speed Spin-Transfer Magnetization Switching in Magnetic Multilayers. Japanese Journal of Applied Physics, 2006, 45, 3842-3845.	1.5	3
115	Macromodeling of Josephson logic circuits. IEEE Transactions on Magnetics, 1983, 19, 1217-1220.	2.1	2
116	Dimensional correction of high dielectric and magnetic constants determined by S parameters measurements. Electronics Letters, 1990, 26, 1151.	1.0	2
117	Electrostatic capacitances in standard and pseudomorphic ultrashort gate length HEMTs. Electronics Letters, 1992, 28, 1776.	1.0	2
118	Gate length electric parameter dependences of ultra-submicrometre $\delta$ -doped pseudomorphic HEMTs. Electronics Letters, 1993, 29, 1570.	1.0	2
119	An electromechanical mixer using silicon micromechanical capacitors and radio-frequency functions. Journal of Micromechanics and Microengineering, 2000, 10, 254-259.	2.6	2
120	Cryosonde IRM : antenne IRM supraconductrice pour la microscopie des régions superficielles du corps humain et des petits modèles animaux. IRBM News, 2004, 25, 254-259.	0.1	2
121	Microwave Noise Performance and Modeling of SiGe-Based HFETs. IEEE Transactions on Electron Devices, 2005, 52, 2409-2415.	3.0	2
122	Germanium on silicon photodetectors for telecom wavelengths. , 2007, , .		2
123	Ge photodetectors integrated in Si waveguides. , 2008, , .		2
124	Carrier depletion based silicon optical modulators. , 2010, , .		2
125	Development of a microwave capacitive method for the spectroscopy of the complex permittivity. Journal of Applied Physics, 2014, 116, 204102.	2.5	2
126	Millimeter-Wave Measurement. , 0, , .		2



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127	Un simulateur temporel pour les circuits picosecondes avec effets de propagation et de couplage : MACPRO. Revue De Physique Appliquée, 1987, 22, 1539-1547.	0.4	2
128	High electric field transport effects on low temperature operation of pseudomorphic HEMTs. European Physical Journal Special Topics, 1994, 04, C6-171-C6-176.	0.2	2
129	Optimization of propagation effects in a superconducting sampler. IEEE Transactions on Magnetics, 1985, 21, 562-565.	2.1	1
130	Design of fast Josephson arithmetic circuits. IEEE Transactions on Magnetics, 1991, 27, 2867-2871.	2.1	1
131	High frequency broadband characterization of metal/high Tc superconducting coplanar structures. Journal of Alloys and Compounds, 1993, 195, 715-718.	5.5	1
132	Low temperature low voltage operation of HEMTs on InP. European Physical Journal Special Topics, 1994, 04, C6-153-C6-158.	0.2	1
133	Reduced timing jitter of two-section 1.55- $\mu$ m laser diodes under gain-loss-switching regime at multigigahertz rates. IEEE Photonics Technology Letters, 1998, 10, 1694-1696.	2.5	1
134	High performance 100 nm T-gate strained Si/Si <sub>0.6</sub> Ge/Si <sub>0.4</sub> n-MODFET. , 0, , .		1
135	Noise in Si/SiGe and Ge/SiGe MODFET. , 2004, 5470, 107.		1
136	Electro-optical intersubband modulators at telecommunication wavelengths based on GaN/AlN quantum wells. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1093-1095.	1.8	1
137	Ge-on-silicon vertical PIN photodetectors. , 2009, , .		1
138	Modulators and photodetectors developed in the framework of the European HELIOS project. Proceedings of SPIE, 2010, , .	0.8	1
139	High speed silicon optical modulator. Proceedings of SPIE, 2010, , .	0.8	1
140	High speed silicon-based optoelectronic devices on 300mm platform. , 2014, , .		1
141	High-Speed Germanium Pin Photodiodes Integrated on Silicon-on-Insulator Nanophotonic Waveguides. , 2019, , .		1
142	SiGe Hetero FETs on silicon at cryogenic temperature. European Physical Journal Special Topics, 2002, 12, 3-10.	0.2	1
143	Speed optimization of Josephson direct coupled logic. Revue De Physique Appliquée, 1990, 25, 443-452.	0.4	1
144	Modèles de lignes simples et couplées, idéales et à pertes, pour la CAO des circuits gigabits. Annales Des Telecommunications/Annals of Telecommunications, 1990, 45, 306-314.	2.5	0

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145	Time domain CAD and measurements of lossy coupled lines. Electronics Letters, 1990, 26, 473.	1.0	0
146	Experimental and theoretical investigation of parameter evolution of ultra-short gate standard and pseudomorphic HEMTs. Microelectronic Engineering, 1992, 19, 313-316.	2.4	0
147	Experimental characterisation and electromagnetic modeling of YBaCuO coplanar lines covered with silver. Physica C: Superconductivity and Its Applications, 1994, 235-240, 3365-3366.	1.2	0
148	High speed Si/SiGe and Ge/SiGe MODFETs. , 0, , .		0
149	Thermal stability of ion-irradiated InGaAs with subpicosecond carrier lifetime. , 2004, , .		0
150	Electro-optic sampling using wide-band high-efficiency ion-irradiated photoconductor as optical-to-electrical converter. , 0, , .		0
151	Noise Behavior of Buried Channel SiGe HFETs for High Speed Circuit&#8217;s Applications. , 0, , .		0
152	A 210-GHz bandwidth electrooptic sampler for large signal characterization of InP-based components. IEEE Photonics Technology Letters, 2005, 17, 2679-2681.	2.5	0
153	1.55 $\mu$ m InP-based electrically-pumped VECSELs: comparison of buried and implanted tunnel junctions as current confinement schemes for the realization of large diameter devices. , 2007, , .		0
154	Germanium photodetector integrated in a Silicon-On-Insulator microwaveguide. , 2007, , .		0
155	2 port vectorial THz electro-optic sampling system. , 2008, , .		0
156	2-port vectorial THz electro-optic sampling system. , 2008, , .		0
157	CW generation up to 2 THz by ion-irradiated In $\times$ 0.53 Ga $\times$ 0.47 As photomixer driven at 1.55 $\mu$ m wavelengths. , 2008, , .		0
158	Transfer of a GHz modulation from an optical carrier at telecom wavelengths to a free space THz beam. , 2009, , .		0
159	Ge-on-silicon waveguide photodetectors for optical telecommunications. Proceedings of SPIE, 2009, , .	0.8	0
160	8 Gb/s 0.5 V integrated Ge-on-SOI photodetector. , 2009, , .		0
161	MEASUREMENT OF NANOSECOND-SCALE SPIN-TRANSFER TORQUE MAGNETIZATION SWITCHING. , 2009, , .		0
162	Properties of planar Goubau waveguides in the THz spectral range. , 2011, , .		0

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163	Comparison of GaAs and DAST electro-optic crystals for THz time domain spectroscopy using 1.55 $\mu$ m fiber laser pulses. Proceedings of SPIE, 2011, , .	0.8	0
164	Low-loss and high extinction ratio 40 Gbit/s optical modulator with self-aligned fabrication process. , 2012, , .		0
165	Confinement of THz surface waves on the subwavelength size metal waveguide. Applied Physics A: Materials Science and Processing, 2012, 109, 993-995.	2.3	0
166	High Performance Ge Photodetectors and Si Modulators for Integrated Photonics. , 2012, , .		0
167	High speed silicon modulators on 300 mm SOI wafers. , 2013, , .		0
168	THz plasmonic waveguides with low-loss and low-group velocity dispersion using flexible thin substrate. , 2013, , .		0
169	40 Gbit/s silicon modulators fabricated on 200-mm and 300-mm SOI wafers. , 2014, , .		0
170	Low Power Consumption and High-Speed Ge Receivers. , 2017, , .		0
171	High-Speed Germanium Pin Photodiodes Integrated on Silicon-on-Insulator Nanophotonic Waveguides. , 2019, , .		0
172	High speed silicon modulators and detectors. , 2012, , .		0
173	Modèle analytique du MESFET AsGa pour simulation de circuits logiques ultra-rapides. Revue De Physique Appliquée, 1987, 22, 1515-1527.	0.4	0
174	Analytical expressions of the turn on delay and the rise time of very fast Josephson junctions. Revue De Physique Appliquée, 1988, 23, 1861-1867.	0.4	0
175	High-performance waveguide photodetectors based on lateral Si/Ge/Si heterojunction. , 2019, , .		0